

Station	Time	Lat.	Long.	Depth	Wind	Temp.	Pressure	State	Remarks
1	0800	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
2	0900	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
3	1000	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
4	1100	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
5	1200	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
6	1300	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
7	1400	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
8	1500	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
9	1600	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
10	1700	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
11	1800	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
12	1900	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
13	2000	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
14	2100	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
15	2200	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
16	2300	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
17	0000	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
18	0100	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
19	0200	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
20	0300	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
21	0400	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
22	0500	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
23	0600	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear
24	0700	34° 15' N	121° 05' E	10	10	20.0	1013.2	B	Clear

A method of isolating piezoelectric thin film acoustic resonator devices to prevent laterally propagating waves generated by the device from leaving the device and/or interfering with adjacent devices or systems. Specifically, this isolation technique involves the manipulation or isolation of the piezoelectric material layer between the acoustic resonator devices, in an effort to limit the amount of acoustic energy which propagates in a lateral direction away from the device. In one aspect, at least a portion of the piezoelectric material not involved in signal transmission by transduction between RF and acoustic energy is removed from the device. In another aspect, the growth of a piezoelectric material is limited to certain regions during fabrication of the device. In a further aspect, the crystal orientation of the piezoelectric material is disrupted or altered during device fabrication so as to form regions having excellent piezoelectric properties and regions exhibiting poor piezoelectric characteristics.